Old Company Name in Catalogs and Other Documents

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Renesas Electronics website: http://www.renesas.com

April 1st, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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DATA SHEET



NEM090853P-28

N-CHANNEL SILICON POWER LDMOS FET FOR UHF-BAND POWER AMPLIFIER

DESCRIPTION

The NEM090853P-28 is an N-channel enhancement-mode lateral MOS FET designed for 0.8 to 1.0 GHz, 90 W single-end power amplifier applications, such as, GSM/EDGE/N-CDMA cellular base station. Dies are manufactured using our NEWMOS technology (our WSi gate lateral MOS FET), and its nitride surface passivation and triple layer aluminum silicon metalization offer a high degree of reliability.

FEATURES

High 1 dB compression output power : Po (1 dB) = 90 W TYP. (VDs = 28 V, IDset = 800 mA, f = 920 to 960 MHz CW)

High linear gain
 : G_L = 19.5 dB TYP. (V_{DS} = 28 V, I_{Dset} = 800 mA, f = 920 to 960 MHz CW)

• High drain efficiency : η_d = 57% TYP. (V_{DS} = 28 V, I_{Dset} = 800 mA, f = 920 to 960 MHz CW)

Low intermodulation distortion
 : IM₃ = -37 dBc TYP. (VDs = 28 V, IDset = 800 mA, f = 960/960.1 MHz,

 $P_{out} = 43 \text{ dBm } (2 \text{ tones})$

: $IM_3 = -45 \text{ dBc TYP}$. $(V_{DS} = 28 \text{ V}, I_{Dset} = 800 \text{ mA}, f = 880/880.1 \text{ MHz},$

Pout = 40 dBm (2 tones))

Internal matched (Input and Output) for ease of use

- · Low cost hollow plastic packages
- 100% screening
- Integrated ESD protection
- Effective prevention against humidity
- Excellent stability against HCI (Hot Carrier Injection)

APPLICATION

Digital cellular base station PA: GSM/EDGE/N-CDMA etc.

ORDERING INFORMATION

Part Number	Package	Supplying Form		
NEM090853P-28 T-97M (3P)		ESD protective envelope		

Remark To order evaluation samples, contact your nearby sales office.

The unit sample quantity is 1 pcs.

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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ABSOLUTE MAXIMUM RATINGS (TA = +25°C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	VDS	65	V
Gate to Source Voltage	V _{GS}	7	V
Drain Current	lσ	10.0	Α
Total Device Dissipation	Ptot Note	250	W
Thermal Resistance	Rth	0.7	°C/W
Channel Temperature	Tch	200	°C
Storage Temperature	Tstg	-65 to +150	°C

Note Tc = 25 °C

RECOMMENDED OPERATING RANGE

Parameter	Symbol	MIN.	TYP.	MAX.	Unit	
Drain to Source Voltage	VDS	-	28	30	V	
Gate to Source Voltage	Vgs	1.5	1.9	2.5	V	Ś
Input Power	Pin	-	32	36	dBm	



ELECTRICAL CHARACTERISTICS (TA = +25°C)

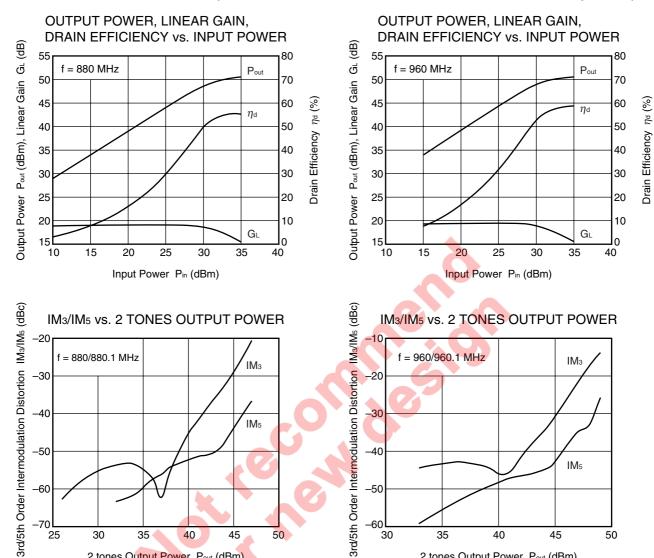
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	Igss	V _{GSS} = 5V	-	=	1	μΑ
Drain to Source Leakage Current (Zero Gate Voltage Drain Current)	Ipss	V _{DSS} = 65 V	ı	ı	1	mA
Gate Threshold Voltage	V_{th}	V _{DS} = 10 V, I _{DS} = 1 mA	1.0	1.4	2.0	V
Transconductance	g™	$V_{DS} = 20 \text{ V}, \text{ lps} = 2 \text{ A} \pm 100 \text{ mA}$	1	4.8	1	S
Drain to Source Breakdown Voltage	BV _{DSS}	$loss = 10 \mu A$	65	75	1	V
Gain 1 dB Compression Output Power	Po (1 dB)	f = 920 to 960 MHz, Pin = 32 dBm,	_	49.5	-	dBm
Linear Gain	GL Note	V _{DS} = 28 V, I _{Dset} = 800 mA	18.5	19.5	_	dB
Output Power	Pout		49.3	50	_	dBm
Drain Efficiency	$\eta_{ extsf{d}}$		50	57	-	%
Power Added Efficiency	η add		4	56	_	%
3rd Order Intermodulation Distortion	IМз	f = 960/960.1 MHz, V _{DS} = 28 V, I _{Dset} = 800 mA, 2 tones P _{out} = 43 dBm		-37	-	dBc
Gain 1 dB Compression Output Power	Po (1 dB)	f = 880 MHz, Pin = 32 dBm,		49.5	-	dBm
Linear Gain	GL ^{Note}	V _{DS} = 28 V, I _{Dset} = 800 mA	5	19.0	_	dB
Output Power	Pout	A 6	-	50	_	dBm
Drain Efficiency	$\eta_{ extsf{d}}$			57		%
Power Added Efficiency	η add	~O, Y _o	1	56	ı	%
3rd Order Intermodulation Distortion	IMз	f = 880/880.1 MHz, V _{DS} = 28 V, I _{Dset} = 800 mA, 2 tones P _{out} = 40 dBm	-	-45	-	dBc

Note $P_{in} = 22 dBm$



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TYPICAL CHARACTERISTICS (TA = +25°C, VDS = 28 V, IDset = 800 mA, unless otherwise specified)



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2 tones Output Power Pout (dBm)

Remark The graphs indicate nominal characteristics.

2 tones Output Power Pout (dBm)

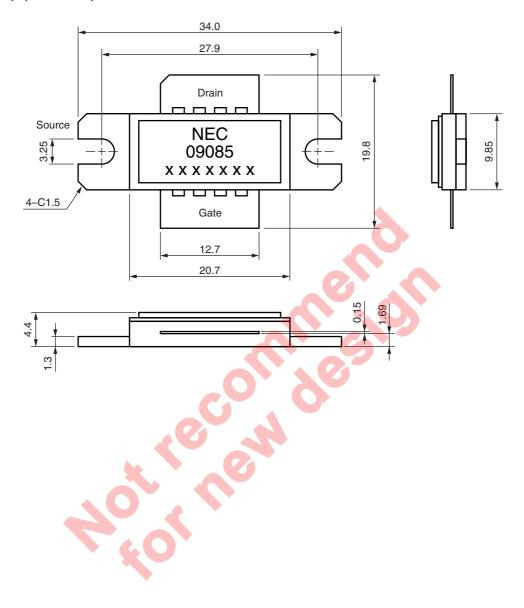
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PACKAGE DIMENSIONS

T-97M (3P) (UNIT: mm)



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RECOMMENDED MOUNTING CONDITIONS FOR CORRECT USE

- (1) Fix to a heat sink or mount surface completely with screws at the two holes of the flange.
- (2) The recommended torque strength of the screws is 29.4 N·cm typical using M3 type screws.
- (3) The recommended flatness of the mount surface is less than $\pm 10~\mu m$ (roughness of surface is $\nabla \nabla \nabla$).

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol	
Partial Heating	Peak temperature (pin temperature) Soldering time (per pin of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350-P3

Caution Do not use different soldering methods together (except for partial heating).



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 - "Standard": Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
 - "Special": Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
 - "Specific": Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems and medical equipment for life support, etc.

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M8E 00.4-0110

NEM090853P-28



▶ For further information, please contact

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